

### AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method for fabricating a ferroelectric memory device, comprising the steps of:

- a1) forming a lower electrode on a predetermined surface of a semiconductor substrate;
  - b1) forming a metal oxide layer over a surface of the lower electrode and a surface of the semiconductor substrate;
  - c1) forming an inter layer dielectric film over the metal oxide layer;
  - d1) performing a blanket etching for the inter layer dielectric film and the metal oxide layer in order to expose an upper surface of the lower electrode; and
  - e1) forming an opening which has a predetermined depth, wherein the opening is obtained by removing only the metal oxide layer between the inter layer dielectric film and the lower electrode through a selective etching process;
- a2) forming a ferroelectric layer on the lower electrode and the inter layer dielectric film; and
- b2) forming an upper electrode on the ferroelectric layer formed on the lower electrode.

Claim 2 (Original): The method as recited in claim 1, wherein the metal oxide layer is formed by using one of an  $\text{Al}_2\text{O}_3$  layer, an  $\text{TiO}_2$  layer, a  $\text{TaO}_2$  layer, a  $\text{ZrO}_2$  layer.

Claim 3 (Original): The method as recited in claim 1, wherein a thickness of the metal oxide layer ranges from about 1 Å to about 500 Å.

Claim 4 (Original): The method as recited in claim 1, wherein a wet etching is carried out by using a selective etching process.

Claim 5 (Original): The method as recited in claim 4, wherein the wet selective etching process is carried out by using an etching solution containing at least one selected from a group of sulfuric acid, nitric acid and phosphoric acid.

Claim 6 (Original): The method as recited in claim 5, wherein a concentration of the etching solution for the wet selective etching process ranges from about 0% to about 50%.

Claim 7 (Original): The method as recited in claim 4, wherein the wet etching process is carried out by using an etching solution containing a ammonia ( $\text{NH}_4\text{OH}$ ) liquid or a hydrogen peroxide ( $\text{H}_2\text{O}_2$ ) liquid.

Claim 8 (Original): The method as recited in claim 7, wherein a concentration of the etching solution containing the ammonia ( $\text{NH}_4\text{OH}$ ) liquid or hydrogen peroxide ( $\text{H}_2\text{O}_2$ ) liquid ranges from about 0% to 50%.

Claim 9 (Canceled)

Claim 10 (Original): The method as recited in claim 1, wherein the lower electrode is constituted sequentially with an platinum (Pt) layer, an iridium oxide ( $\text{IrOx}$ ) layer and an iridium (Ir) layer.

Claim 11 (Original): The method as recited in claim 10, wherein the ferroelectric layer is constituted with one of materials of  $(\text{Bi}, \text{La})_4\text{Ti}_3\text{O}_{12}$  (BLT),  $\text{SrBi}_2\text{Ta}_2\text{O}_9$  (SBT),  $\text{SrBi}_2(\text{Ta}_{1-x}\text{Nb}_x)_2\text{O}_9$  (SBTN), and  $(\text{Pb}, \text{Zr})\text{TiO}_3$  (PZT).